

Susanne Stemmer

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

306
papers

13,347
citations

58
h-index

101
g-index

314
ext. papers

14,502
ext. citations

4.2
avg, IF

6.57
L-index

#	Paper	IF	Citations
306	Resonant x-ray scattering method for measuring cation stoichiometry in BaSnO ₃ thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 013411	2.9	1
305	Hybrid oxide molecular beam epitaxy 2022 , 53-74		
304	Molecular beam epitaxy of phase-pure antiperovskite Sr ₃ SnO thin films. <i>Applied Physics Letters</i> , 2021 , 119, 161903	3.4	1
303	Role of locally polar regions in the superconductivity of SrTiO ₃ . <i>Physical Review Materials</i> , 2021 , 5,	3.2	1
302	Reducing surface depletion of superconducting SrTiO ₃ films with EuTiO ₃ capping layers. <i>Applied Physics Letters</i> , 2021 , 119, 162601	3.4	1
301	Detecting topological phase transitions in cadmium arsenide films via the transverse magnetoresistance. <i>Applied Physics Letters</i> , 2021 , 119, 171907	3.4	1
300	Room-Temperature Spin Transport in CdAs. <i>ACS Nano</i> , 2021 , 15, 5459-5466	16.7	1
299	Probing charge pumping and relaxation of the chiral anomaly in a Dirac semimetal. <i>Science Advances</i> , 2021 , 7,	14.3	5
298	Superconductivity in magnetically doped SrTiO ₃ . <i>Applied Physics Letters</i> , 2021 , 118, 202602	3.4	2
297	Controlling the symmetry of cadmium arsenide films by epitaxial strain. <i>APL Materials</i> , 2021 , 9, 051111	5.7	0
296	Quantum Hall effect of the topological insulator state of cadmium arsenide in Corbino geometry. <i>Applied Physics Letters</i> , 2021 , 118, 261901	3.4	0
295	Electron transport of perovskite oxide BaSnO ₃ on (110) DyScO ₃ substrate with channel-recess for ferroelectric field effect transistors. <i>Applied Physics Letters</i> , 2021 , 118, 042105	3.4	2
294	Interplay between Polar Distortions and Superconductivity in SrTiO ₃ . <i>Microscopy and Microanalysis</i> , 2021 , 27, 360-362	0.5	
293	Probing the Polar Instability of Strained SrTiO ₃ with HAADF-STEM. <i>Microscopy and Microanalysis</i> , 2020 , 26, 2474-2476	0.5	
292	Relating Crystal Symmetry to Topological Phases: Convergent Beam Electron Diffraction Studies of the Dirac Semimetal Cd ₃ As ₂ . <i>Microscopy and Microanalysis</i> , 2020 , 26, 3034-3037	0.5	
291	Carrier mobilities of (001) cadmium arsenide films. <i>APL Materials</i> , 2020 , 8, 051106	5.7	8
290	Carbon impurity concentrations in BaSnO ₃ films grown by molecular beam epitaxy using a tin oxide source. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 043405	2.9	

289	High-Current Perovskite Oxide BaTiO ₃ /BaSnO ₃ Heterostructure Field Effect Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 41, 621-624	4.4	5
288	Efficient Terahertz Harmonic Generation with Coherent Acceleration of Electrons in the Dirac Semimetal Cd ₃ As ₂ . <i>Physical Review Letters</i> , 2020 , 124, 117402	7.4	50
287	Possible signatures of mixed-parity superconductivity in doped polar SrTiO ₃ films. <i>Physical Review B</i> , 2020 , 101,	3.3	14
286	Hydrothermal growth of BaSnO ₃ single crystals for wide bandgap applications. <i>Journal of Crystal Growth</i> , 2020 , 536, 125529	1.6	7
285	Topological Insulator State and Collapse of the Quantum Hall Effect in a Three-Dimensional Dirac Semimetal Heterojunction. <i>Physical Review X</i> , 2020 , 10,	9.1	9
284	Widely Tunable Optical and Thermal Properties of Dirac Semimetal Cd ₃ As ₂ . <i>Advanced Optical Materials</i> , 2020 , 8, 1901192	8.1	15
283	High Current Density SmTiO ₃ /SrTiO ₃ Field-Effect Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 510-516	4	4
282	Stoichiometry control in molecular beam epitaxy of BaSnO ₃ . <i>Physical Review Materials</i> , 2020 , 4,	3.2	5
281	Correlating magnetic structure and magnetotransport in semimetal thin films of Eu Sm TiO. <i>Physical Review Materials</i> , 2020 , 4,	3.2	2
280	Nanoscale etching of perovskite oxides for field effect transistor applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 012201	1.3	6
279	Prospects of Terahertz Transistors with the Topological Semimetal Cadmium Arsenide. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000676	6.4	6
278	Polar Nanodomains in a Ferroelectric Superconductor. <i>Nano Letters</i> , 2020 , 20, 6542-6547	11.5	8
277	Topological surface states in strained Dirac semimetal thin films. <i>Physical Review B</i> , 2020 , 102,	3.3	4
276	Magnetoresistance effects in cadmium arsenide thin films. <i>Applied Physics Letters</i> , 2020 , 117, 170601	3.4	
275	Order-Disorder Ferroelectric Transition of Strained SrTiO ₃ . <i>Physical Review Letters</i> , 2020 , 125, 087601	7.4	13
274	Velocity saturation in La-doped BaSnO ₃ thin films. <i>Applied Physics Letters</i> , 2019 , 115, 092102	3.4	7
273	Absence of signatures of Weyl orbits in the thickness dependence of quantum transport in cadmium arsenide. <i>Physical Review B</i> , 2019 , 99,	3.3	4
272	Enhancing superconductivity in SrTiO films with strain. <i>Science Advances</i> , 2019 , 5, eaaw0120	14.3	77

271	Field-effect transistors with the three-dimensional Dirac semimetal cadmium arsenide. <i>Applied Physics Letters</i> , 2019 , 115, 062101	3.4	6
270	Probing the Local Lattice Distortions in Doped SrTiO ₃ Using Quantitative STEM. <i>Microscopy and Microanalysis</i> , 2019 , 25, 976-977	0.5	
269	Basal-plane growth of cadmium arsenide by molecular beam epitaxy. <i>Physical Review Materials</i> , 2019 , 3,	3.2	14
268	Surface states of strained thin films of the Dirac semimetal Cd ₃ As ₂ . <i>Physical Review Materials</i> , 2019 , 3,	3.2	15
267	Point group symmetry of cadmium arsenide thin films determined by convergent beam electron diffraction. <i>Physical Review Materials</i> , 2019 , 3,	3.2	4
266	Ferroelectric enhancement of superconductivity in compressively strained SrTiO ₃ films. <i>Physical Review Materials</i> , 2019 , 3,	3.2	23
265	Lattice relaxations around individual dopant atoms in SrTiO ₃ . <i>Physical Review Materials</i> , 2019 , 3,	3.2	4
264	Soft phonons and ultralow lattice thermal conductivity in the Dirac semimetal Cd ₃ As ₂ . <i>Physical Review Research</i> , 2019 , 1,	3.9	13
263	Controlling a Van Hove singularity and Fermi surface topology at a complex oxide heterostructure interface. <i>Nature Communications</i> , 2019 , 10, 5534	17.4	4
262	Anisotropic magnetoresistance in the itinerant antiferromagnetic EuTiO ₃ . <i>Physical Review B</i> , 2019 , 99,	3.3	21
261	Design of Transistors Using High-Permittivity Materials. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 896-900	2.9	23
260	Thickness dependence of the quantum Hall effect in films of the three-dimensional Dirac semimetal Cd ₃ As ₂ . <i>APL Materials</i> , 2018 , 6, 026105	5.7	38
259	Quasistatic antiferromagnetism in the quantum wells of SmTiO ₃ /SrTiO ₃ heterostructures. <i>Npj Quantum Materials</i> , 2018 , 3,	5	7
258	Non-Fermi liquids in oxide heterostructures. <i>Reports on Progress in Physics</i> , 2018 , 81, 062502	14.4	15
257	Observation of the Quantum Hall Effect in Confined Films of the Three-Dimensional Dirac Semimetal Cd ₃ As ₂ . <i>Physical Review Letters</i> , 2018 , 120, 016801	7.4	99
256	Electron nematic fluid in a strained Sr ₃ Ru ₂ O ₇ film. <i>Physical Review B</i> , 2018 , 97,	3.3	6
255	Octahedral tilt independent magnetism in confined GdTiO ₃ films. <i>Applied Physics Letters</i> , 2018 , 112, 132407	3.4	1
254	Two-dimensional Dirac fermions in thin films of Cd ₃ As ₂ . <i>Physical Review B</i> , 2018 , 97,	3.3	30

253	Spontaneous Hall effects in the electron system at the SmTiO ₃ /EuTiO ₃ interface. <i>APL Materials</i> , 2018 , 6, 056102	5.7	17
252	Resolving interfacial charge transfer in titanate superlattices using resonant x-ray reflectometry. <i>Physical Review Materials</i> , 2018 , 2,	3.2	1
251	Nitrogen surface passivation of the Dirac semimetal Cd ₃ As ₂ . <i>Physical Review Materials</i> , 2018 , 2,	3.2	9
250	Carrier density control of magnetism and Berry phases in doped EuTiO ₃ . <i>APL Materials</i> , 2018 , 6, 056105	5.7	18
249	Electric field effect near the metal-insulator transition of a two-dimensional electron system in SrTiO ₃ . <i>Applied Physics Letters</i> , 2017 , 110, 062104	3.4	24
248	Potential Fluctuations at Low Temperatures in Mesoscopic-Scale SmTiO/SrTiO/SmTiO Quantum Well Structures. <i>ACS Nano</i> , 2017 , 11, 3760-3766	16.7	
247	BaTiO ₃ /SrTiO ₃ heterostructures for ferroelectric field effect transistors. <i>Applied Physics Letters</i> , 2017 , 110, 232902	3.4	24
246	HAADF-STEM Study of MBE-Grown Dirac Semimetal Cd ₃ As ₂ . <i>Microscopy and Microanalysis</i> , 2017 , 23, 1480-1481	0.5	
245	Probing Disorder in MBE-grown Oxide Films Using Quantitative STEM. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1578-1579	0.5	
244	Response of the Lattice across the Filling-Controlled Mott Metal-Insulator Transition of a Rare Earth Titanate. <i>Physical Review Letters</i> , 2017 , 119, 186803	7.4	4
243	Disorder versus two transport lifetimes in a strongly correlated electron liquid. <i>Scientific Reports</i> , 2017 , 7, 10312	4.9	2
242	Evidence of a topological Hall effect in Eu ^{1-x} Sm _x TiO ₃ . <i>Applied Physics Letters</i> , 2017 , 111, 172403	3.4	41
241	Novel Metal-Insulator Transition at the SmTiO ₃ /SrTiO ₃ Interface. <i>Physical Review Letters</i> , 2017 , 118, 236803	7.4	30
240	Negative magnetoresistance due to conductivity fluctuations in films of the topological semimetal Cd ₃ As ₂ . <i>Physical Review B</i> , 2017 , 95,	3.3	40
239	Imaging Point Defects in Complex Oxides Using Quantitative STEM. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1568-1569	0.5	
238	Effect of BST film thickness on the performance of tunable interdigital capacitors grown by MBE. <i>Applied Physics Letters</i> , 2017 , 111, 262903	3.4	11
237	Growth of strontium ruthenate films by hybrid molecular beam epitaxy. <i>APL Materials</i> , 2017 , 5, 096101	5.7	12
236	Pseudogaps and Emergence of Coherence in Two-Dimensional Electron Liquids in SrTiO ₃ . <i>Physical Review Letters</i> , 2016 , 117, 046402	7.4	11

235	Energetic, spatial, and momentum character of the electronic structure at a buried interface: The two-dimensional electron gas between two metal oxides. <i>Physical Review B</i> , 2016 , 93,	3-3	22
234	Depth-Resolved Composition and Electronic Structure of Buried Layers and Interfaces in a LaNiO ₃ /SrTiO ₃ Superlattice from Soft- and Hard- X-ray Standing-Wave Angle-Resolved Photoemission. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2016 , 211, 70-81	1-7	8
233	Key role of lattice symmetry in the metal-insulator transition of NdNiO ₃ films. <i>Scientific Reports</i> , 2016 , 6, 23652	4-9	22
232	Direct Observation of Sr Vacancies in SrTiO ₃ by Quantitative Scanning Transmission Electron Microscopy. <i>Physical Review X</i> , 2016 , 6,	9-1	21
231	Large electron concentration modulation using capacitance enhancement in SrTiO ₃ /SmTiO ₃ Fin-field effect transistors. <i>Applied Physics Letters</i> , 2016 , 108, 183509	3-4	3
230	(Ba,Sr)TiO ₃ tunable capacitors with RF commutation quality factors exceeding 6000. <i>Applied Physics Letters</i> , 2016 , 109, 112902	3-4	25
229	Carrier density independent scattering rate in SrTiO ₃ -based electron liquids. <i>Scientific Reports</i> , 2016 , 6, 20865	4-9	31
228	Role of film stoichiometry and interface quality in the performance of (Ba,Sr)TiO ₃ tunable capacitors with high figures of merit. <i>Applied Physics Letters</i> , 2016 , 109, 192904	3-4	15
227	Structure and optical band gaps of (Ba,Sr)SnO ₃ films grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 050601	2-9	34
226	Band alignments between SmTiO ₃ , GdTiO ₃ , and SrTiO ₃ . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 061102	2-9	5
225	Conduction band edge effective mass of La-doped BaSnO ₃ . <i>Applied Physics Letters</i> , 2016 , 108, 252107	3-4	33
224	Molecular beam epitaxy of Cd ₃ As ₂ on a III-V substrate. <i>APL Materials</i> , 2016 , 4, 126110	5-7	47
223	Two-port tunable interdigital capacitors fabricated on low-loss MBE-grown Ba _{0.29} Sr _{0.71} TiO ₃ 2016 ,		1
222	High-mobility BaSnO ₃ grown by oxide molecular beam epitaxy. <i>APL Materials</i> , 2016 , 4, 016106	5-7	148
221	Probing the Metal-Insulator Transition in BaTiO ₃ by Electrostatic Doping. <i>Physical Review Letters</i> , 2016 , 117, 037602	7-4	28
220	Interface-Driven Ferromagnetism within the Quantum Wells of a Rare Earth Titanate Superlattice. <i>Physical Review Letters</i> , 2016 , 117, 037205	7-4	10
219	0.5 V Supply Voltage Operation of In _{0.65} Ga _{0.35} As/GaAs _{0.4} Sb _{0.6} Tunnel FET. <i>IEEE Electron Device Letters</i> , 2015 , 36, 20-22	4-4	38
218	Determination of the Mott-Hubbard gap in GdTiO ₃ . <i>Physical Review B</i> , 2015 , 92,	3-3	11

217	Tailoring resistive switching in Pt/SrTiO ₃ junctions by stoichiometry control. <i>Scientific Reports</i> , 2015 , 5, 11079	4.9	31
216	Limitations to the room temperature mobility of two- and three-dimensional electron liquids in SrTiO ₃ . <i>Applied Physics Letters</i> , 2015 , 106, 062102	3.4	41
215	Small hole polarons in rare-earth titanates. <i>Applied Physics Letters</i> , 2015 , 106, 232103	3.4	18
214	The electrochemical impact on electrostatic modulation of the metal-insulator transition in nickelates. <i>Applied Physics Letters</i> , 2015 , 106, 122102	3.4	21
213	Two-dimensional electron liquid at the (111) SmTiO ₃ /SrTiO ₃ interface. <i>Applied Physics Letters</i> , 2015 , 106, 132104	3.4	18
212	Correlation between stoichiometry, strain, and metal-insulator transitions of NdNiO ₃ films. <i>Applied Physics Letters</i> , 2015 , 106, 092104	3.4	47
211	Emergence of room-temperature ferroelectricity at reduced dimensions. <i>Science</i> , 2015 , 349, 1314-7	33.3	198
210	Separation of transport lifetimes in SrTiO ₃ -based two-dimensional electron liquids. <i>Physical Review B</i> , 2015 , 91,	3.3	22
209	Dielectric response of metal/SrTiO ₃ /two-dimensional electron liquid heterostructures. <i>Applied Physics Letters</i> , 2015 , 107, 072905	3.4	3
208	Variable-angle high-angle annular dark-field imaging: application to three-dimensional dopant atom profiling. <i>Scientific Reports</i> , 2015 , 5, 12419	4.9	23
207	Gaps and pseudogaps in perovskite rare earth nickelates. <i>APL Materials</i> , 2015 , 3, 062503	5.7	25
206	Observation by resonant angle-resolved photoemission of a critical thickness for 2-dimensional electron gas formation in SrTiO ₃ embedded in GdTiO ₃ . <i>Applied Physics Letters</i> , 2015 , 107, 231602	3.4	8
205	Ferroelectric transition in compressively strained SrTiO ₃ thin films. <i>Applied Physics Letters</i> , 2015 , 107, 192908	3.4	30
204	In-situ nitrogen plasma passivation of Al ₂ O ₃ /GaN interface states. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 020602	2.9	12
203	Tuning bad metal and non-Fermi liquid behavior in a Mott material: Rare-earth nickelate thin films. <i>Science Advances</i> , 2015 , 1, e1500797	14.3	76
202	Two-Dimensional Electron Gases at Complex Oxide Interfaces. <i>Annual Review of Materials Research</i> , 2014 , 44, 151-171	12.8	130
201	Element specific monolayer depth profiling. <i>Advanced Materials</i> , 2014 , 26, 6554-9	24	45
200	Correlation between metal-insulator transitions and structural distortions in high-electron-density SrTiO ₃ quantum wells. <i>Physical Review B</i> , 2014 , 89,	3.3	35

199	Quantum critical behaviour in confined SrTiO ₃ quantum wells embedded in antiferromagnetic SmTiO ₃ . <i>Nature Communications</i> , 2014 , 5, 4258	17.4	41
198	Resistive switching and its suppression in Pt/Nb:SrTiO ₃ junctions. <i>Nature Communications</i> , 2014 , 5, 3990	17.4	138
197	S5-H6: Leakage current suppression in InGaAs-channel MOSFETs: Recessed InP source/drain spacers and InP channel caps 2014 ,		1
196	Formation of InGaAs fins by atomic layer epitaxy on InP sidewalls. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 065503	1.4	3
195	Alleviating polarity-conflict at the heterointerfaces of KTaO ₃ /GdScO ₃ polar complex-oxides. <i>Applied Physics Letters</i> , 2014 , 105, 102901	3.4	10
194	Modulation of over 10 ¹⁴ cm ⁻² electrons in SrTiO ₃ /GdTiO ₃ heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 182904	3.4	35
193	Extremely scaled high-k/In _{0.53} Ga _{0.47} As gate stacks with low leakage and low interface trap densities. <i>Journal of Applied Physics</i> , 2014 , 116, 124104	2.5	21
192	Intrinsic Mobility Limiting Mechanisms in Lanthanum-Doped Strontium Titanate. <i>Physical Review Letters</i> , 2014 , 112,	7.4	78
191	Au-gated SrTiO ₃ field-effect transistors with large electron concentration and current modulation. <i>Applied Physics Letters</i> , 2014 , 105, 113512	3.4	18
190	Highly Scalable Raised Source/Drain InAs Quantum Well MOSFETs Exhibiting $I_{ON}/I_{OFF} = 482$ at $I_{DD} = 100$ nA and $V_{DD} = 0.5$ V. <i>IEEE Electron Device Letters</i> , 2014 , 35, 621-623	4.4	20
189	Scaled ZrO ₂ dielectrics for In _{0.53} Ga _{0.47} As gate stacks with low interface trap densities. <i>Applied Physics Letters</i> , 2014 , 104, 182912	3.4	18
188	Nanostructure investigations of nonlinear differential conductance in NdNiO ₃ thin films. <i>Physical Review B</i> , 2014 , 90,	3.3	5
187	Surface reconstructions in molecular beam epitaxy of SrTiO ₃ . <i>Applied Physics Letters</i> , 2014 , 105, 191901	3.4	33
186	Interface-induced magnetism in perovskite quantum wells. <i>Physical Review B</i> , 2013 , 88,	3.3	53
185	Magnetism and local structure in low-dimensional Mott insulating GdTiO ₃ . <i>Physical Review B</i> , 2013 , 88,	3.3	22
184	Three-dimensional imaging of individual dopant atoms in SrTiO ₃ . <i>Physical Review Letters</i> , 2013 , 111, 266401	7.0	72
183	Nitrogen-passivated dielectric/InGaAs interfaces with sub-nm equivalent oxide thickness and low interface trap densities. <i>Applied Physics Letters</i> , 2013 , 102, 022907	3.4	66
182	High transconductance surface channel In _{0.53} Ga _{0.47} As MOSFETs using MBE source-drain regrowth and surface digital etching 2013 ,		3

181	Symmetry lowering in extreme-electron-density perovskite quantum wells. <i>Physical Review Letters</i> , 2013 , 110, 256401	7.4	46
180	Spin injection and detection in lanthanum- and niobium-doped SrTiO ₃ using the Hanle technique. <i>Nature Communications</i> , 2013 , 4, 2134	17.4	42
179	La-doped SrTiO ₃ films with large cryogenic thermoelectric power factors. <i>Applied Physics Letters</i> , 2013 , 102, 182101	3.4	74
178	Quantum confinement in oxide quantum wells. <i>MRS Bulletin</i> , 2013 , 38, 1032-1039	3.2	34
177	Structural origins of the properties of rare earth nickelate superlattices. <i>Physical Review B</i> , 2013 , 87,	3.3	59
176	Growth window and effect of substrate symmetry in hybrid molecular beam epitaxy of a Mott insulating rare earth titanate. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 041503	2.9	47
175	Subband structure of two-dimensional electron gases in SrTiO ₃ . <i>Applied Physics Letters</i> , 2013 , 103, 212103	3.4	10
174	Two-dimensional electron gas in a modulation-doped SrTiO ₃ /Sr(Ti, Zr)O ₃ heterostructure. <i>Applied Physics Letters</i> , 2013 , 103, 082120	3.4	27
173	Reduction of leakage current in In _{0.53} Ga _{0.47} As channel metal-oxide-semiconductor field-effect-transistors using AlAs _{0.56} Sb _{0.44} confinement layers. <i>Applied Physics Letters</i> , 2013 , 103, 203502	3.4	6
172	Conduction-band edge and Shubnikov-de Haas effect in low-electron-density SrTiO ₃ . <i>Physical Review B</i> , 2013 , 88,	3.3	48
171	High performance raised source/drain InAs/In _{0.53} Ga _{0.47} As channel metal-oxide-semiconductor field-effect-transistors with reduced leakage using a vertical spacer. <i>Applied Physics Letters</i> , 2013 , 103, 233503	3.4	36
170	High-density two-dimensional small polaron gas in a delta-doped Mott insulator. <i>Scientific Reports</i> , 2013 , 3, 3284	4.9	22
169	Influence of plasma-based in-situ surface cleaning procedures on HfO ₂ /In _{0.53} Ga _{0.47} As gate stack properties. <i>Journal of Applied Physics</i> , 2013 , 114, 154108	2.5	20
168	Temperature-dependence of the Hall coefficient of NdNiO ₃ thin films. <i>Applied Physics Letters</i> , 2013 , 103, 182105	3.4	26
167	Toward an artificial Mott insulator: Correlations in confined high-density electron liquids in SrTiO ₃ . <i>Physical Review B</i> , 2012 , 86,	3.3	58
166	Carrier-Controlled Ferromagnetism in SrTiO ₃ . <i>Physical Review X</i> , 2012 , 2,	9.1	63
165	Frequency dispersion in III-V metal-oxide-semiconductor capacitors. <i>Applied Physics Letters</i> , 2012 , 100, 233510	3.4	45
164	Effects of doping on the lattice parameter of SrTiO ₃ . <i>Applied Physics Letters</i> , 2012 , 100, 262104	3.4	90

163	Growth and properties of GdTiO ₃ films prepared by hybrid molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2012 , 355, 166-170	1.6	36
162	Fixed charge in high-k/GaN metal-oxide-semiconductor capacitor structures. <i>Applied Physics Letters</i> , 2012 , 101, 102905	3-4	53
161	Substitutional-Gate MOSFETs With Composite $(\text{In}_{0.53}\text{Ga}_{0.47}\text{As})/\text{InAs}/(\text{In}_{0.53}\text{Ga}_{0.47}\text{As})$ Channels and Self-Aligned MBE Source/Drain Regrowth. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1553-1555	4-4	8
160	Coalescence of InP Epitaxial Lateral Overgrowth by MOVPE with V/III Ratio Variation. <i>Journal of Electronic Materials</i> , 2012 , 41, 845-852	1-9	9
159	Electric field-tunable Ba _x Sr _{1-x} TiO ₃ films with high figures of merit grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012 , 101, 252906	3-4	39
158	Seebeck coefficient of a quantum confined, high-electron-density electron gas in SrTiO ₃ . <i>Applied Physics Letters</i> , 2012 , 100, 161601	3-4	14
157	Quantum oscillations from a two-dimensional electron gas at a Mott/band insulator interface. <i>Applied Physics Letters</i> , 2012 , 101, 151604	3-4	31
156	Modulation doping to control the high-density electron gas at a polar/non-polar oxide interface. <i>Applied Physics Letters</i> , 2012 , 101, 111604	3-4	15
155	Nanoscale quantification of octahedral tilts in perovskite films. <i>Applied Physics Letters</i> , 2012 , 100, 191909	3-4	53
154	Capacitance-voltage analysis of high-carrier-density SrTiO ₃ /GdTiO ₃ heterostructures. <i>Applied Physics Letters</i> , 2012 , 100, 232106	3-4	9
153	Application to Semiconductors 2011 , 523-536		
152	Electrostatic carrier doping of GdTiO ₃ /SrTiO ₃ interfaces. <i>Applied Physics Letters</i> , 2011 , 99, 232116	3-4	195
151	Thermal conductivity as a metric for the crystalline quality of SrTiO ₃ epitaxial layers. <i>Applied Physics Letters</i> , 2011 , 98, 221904	3-4	55
150	Determining ferroelectric polarity at the nanoscale. <i>Applied Physics Letters</i> , 2011 , 98, 052904	3-4	31
149	Charged Defect Quantification in Pt _{1-x} Al _{2O₃} _{1-x} 0.53Ga _{0.47} As _{1-x} HP MOS Capacitors. <i>Journal of the Electrochemical Society</i> , 2011 , 158, G103	3-9	30
148	Transport in ferromagnetic GdTiO ₃ /SrTiO ₃ heterostructures. <i>Applied Physics Letters</i> , 2011 , 98, 112110	3-4	58
147	A heterojunction modulation-doped Mott transistor. <i>Journal of Applied Physics</i> , 2011 , 110, 084503	2-5	52
146	Thermal diffuse scattering in transmission electron microscopy. <i>Ultramicroscopy</i> , 2011 , 111, 1670-80	3-1	27

145	Electrical properties of Er-doped In _{0.53} Ga _{0.47} As. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 03C117	1.3	10
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